

# AD30P30D3

datasheet

$V_{DSS}$	-30V
$R_{DS(on)}(typ.)$	14.5m $\Omega$
$I_D$	-30A
$P_D$	27W

## Features

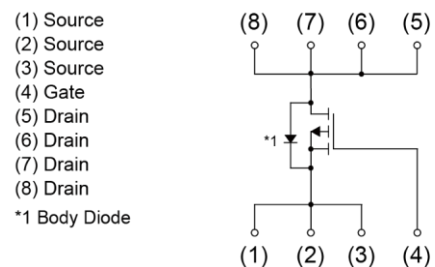
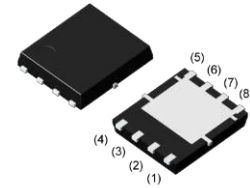
- - 30V, -30A,  $R_{DS(ON)} = 14.5m\Omega @ V_{GS} = 10V$
- Improved  $dv/dt$  capability
- Fast switching
- 100% EAS Guaranteed
- Green Device Available

## Applications

- Networking
- Load Switch
- LED applications
- Quick Charger

## Outline

P PAK 3x3



Type	Reel size (mm)	330
	Tape width (mm)	12
	Basic ordering unit (pcs)	5000
	Taping code	D3
	Marking	AD30P30D3

## Absolute Maximum Ratings $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	-30	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current – Continuous ( $T_c=25^\circ\text{C}$ )	-30	A
	Drain Current – Continuous ( $T_c=100^\circ\text{C}$ )	-19	A
$I_{DM}$	Drain Current – Pulsed <sup>1</sup>	-120	A
$P_D$	Power Dissipation ( $T_c=25^\circ\text{C}$ )	27	W
	Power Dissipation – Derate above $25^\circ\text{C}$	0.22	W/ $^\circ\text{C}$
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

## Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	4.6	$^\circ\text{C}/\text{W}$

## Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)

### Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-30	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =-1mA	---	-0.03	---	V/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =-27V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	-1	uA
		V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V, T <sub>J</sub> =125°C	---	---	-10	uA
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA

### On Characteristics

R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =-10V, I <sub>D</sub> =-8A	---	14.5	18	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-6A	---	23	30	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =-250uA	-1.2	-1.6	-2.5	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	4	---	mV/°C
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =-10V, I <sub>D</sub> =-8A	---	6.8	---	S

### Dynamic and switching Characteristics

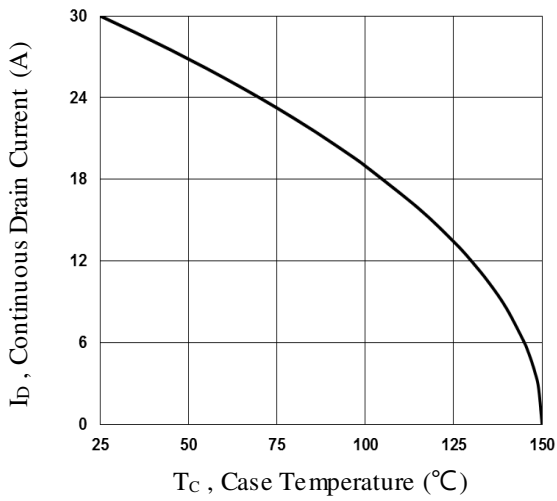
Q <sub>g</sub>	Total Gate Charge <sup>2,3</sup>	V <sub>DS</sub> =-15V, V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-5A	---	11	17	nC
Q <sub>gs</sub>	Gate-Source Charge <sup>2,3</sup>		---	3.4	6	
Q <sub>gd</sub>	Gate-Drain Charge <sup>2,3</sup>		---	4.2	8	
T <sub>d(on)</sub>	Turn-On Delay Time <sup>2,3</sup>	V <sub>DD</sub> =-15V, V <sub>GS</sub> =-10V, R <sub>G</sub> =6Ω I <sub>D</sub> =-1A	---	5.8	11	ns
T <sub>r</sub>	Rise Time <sup>2,3</sup>		---	18.8	36	
T <sub>d(off)</sub>	Turn-Off Delay Time <sup>2,3</sup>		---	46.9	90	
T <sub>f</sub>	Fall Time <sup>2,3</sup>		---	12.3	23	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, F=1MHz	---	1250	2500	pF
C <sub>oss</sub>	Output Capacitance		---	160	320	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	90	180	

### Drain-Source Diode Characteristics and Maximum Ratings

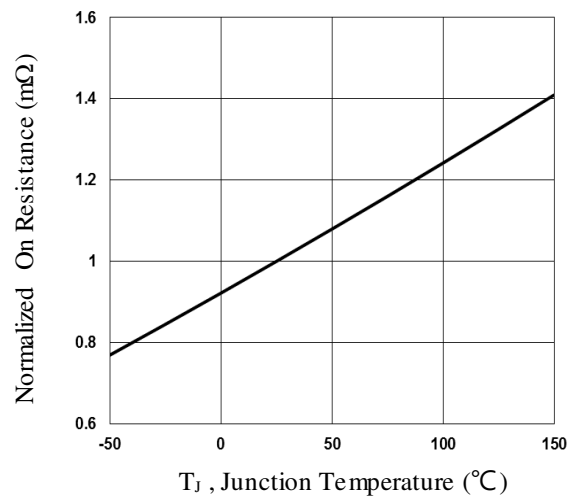
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	-30	A
I <sub>SM</sub>	Pulsed Source Current		---	---	-60	A
V <sub>SD</sub>	Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =-1A, T <sub>J</sub> =25°C	---	---	-1	V

Note :

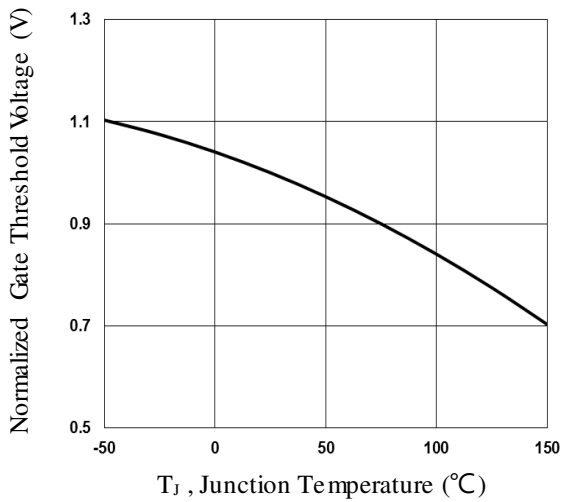
- 1.Repetitive Rating : Pulsed width limited by maximum junction temperature.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%.
- 3.Essentially independent of operating temperature.



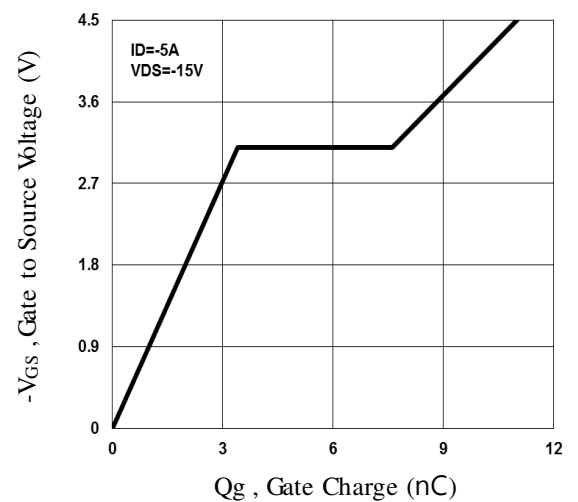
**Fig.1 Continuous Drain Current vs. T<sub>c</sub>**



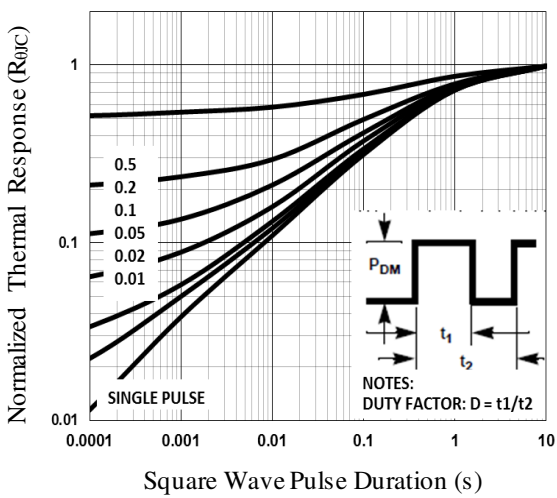
**Fig.2 Normalized RDS(on) vs. T<sub>j</sub>**



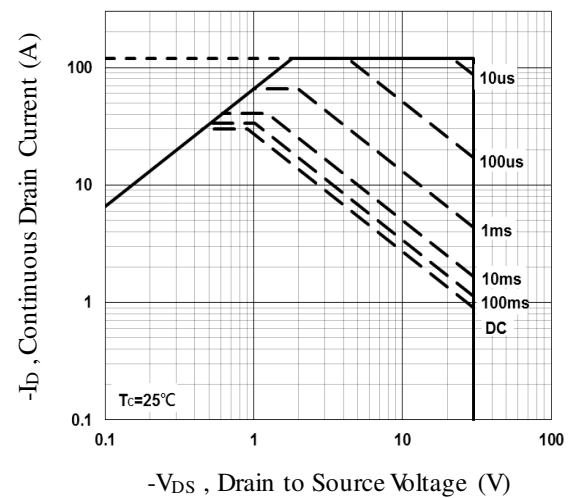
**Fig.3 Normalized V<sub>th</sub> vs. T<sub>j</sub>**



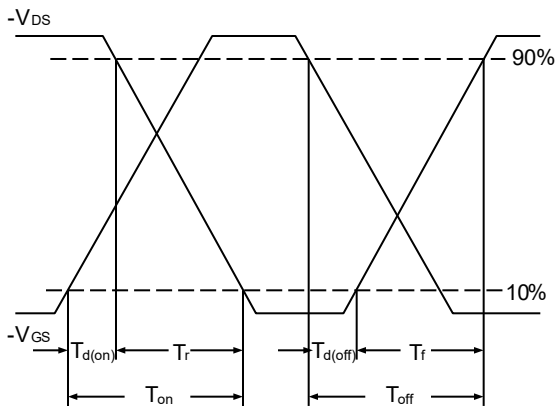
**Fig.4 Gate Charge Waveform**



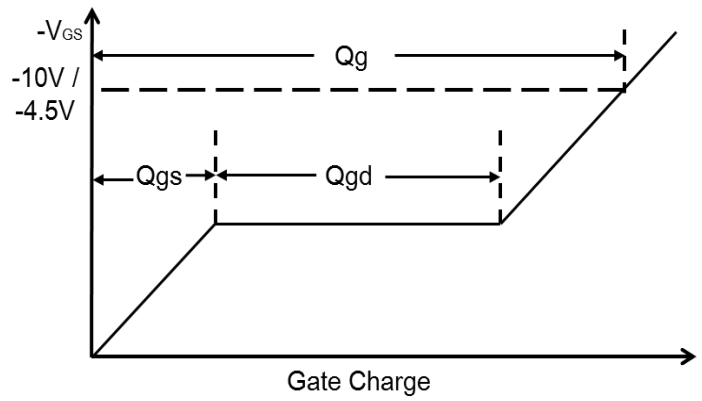
**Fig.5 Normalized Transient Impedance**



**Fig.6 Maximum Safe Operation Area**

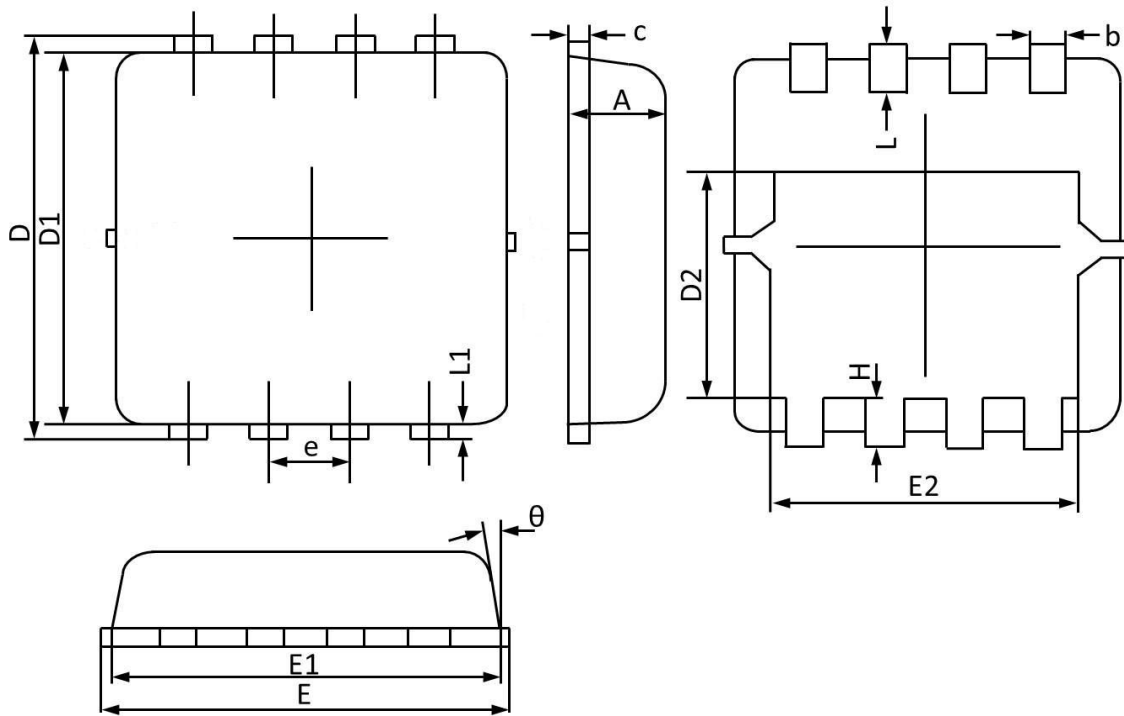


**Fig.7**  
**Switching Time Waveform**



**Fig.8** **Gate Charge Waveform**

## PPAK3x3 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	0.900	0.700	0.035	0.028
b	0.350	0.240	0.014	0.009
c	0.250	0.100	0.010	0.004
D	3.450	3.050	0.136	0.120
D1	3.200	2.900	0.126	0.114
D2	1.850	1.350	0.073	0.053
E	3.400	3.000	0.134	0.118
E1	3.250	2.900	0.128	0.114
E2	2.600	2.350	0.102	0.093
e	0.65BSC		0.026BSC	
H	0.500	0.300	0.020	0.012
L	0.500	0.300	0.020	0.012
L1	0.200	0.070	0.008	0.003
θ	12°	0°	12°	0°